

IN THE SPECIFICATION:

Please replace paragraph [0025] with the following amended paragraph:

[0025] An example of a deposition process includes depositing on the substrate 3000 300, a cladding layer 310 of silicon dioxide doped with boron and phosphorous (BPSG) by introducing tetraethyloxysilane ($\text{Si}(\text{OC}_2\text{H}_5)_4$), (TEOS) at a flow rate of about 700 mgm, triethylborate (TEB) at a flow rate of about 230 mgm, ~~triethylphosphate~~ triethylphosphate (TEPO) at a flow of about 42 mgm, oxygen gas at a flow rate of about 650 sccm, and an inert gas at a flow rate of about 600 sccm, into a PECVD reactor maintained at a temperature between about 350°C and about 550°C, for example, between about 400°C and about 480°C, at a chamber pressure of 9 Torr and generating a plasma at an RF power of about 1150 watts to deposit a layer having a thickness of about 5 microns that can be deposited in about 5 minutes, a deposition rate of about 1 micron/min.